
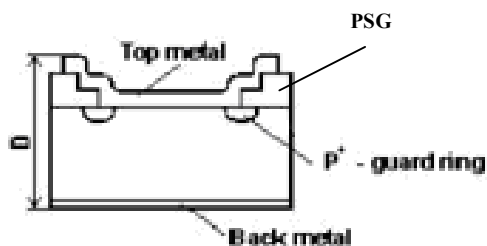
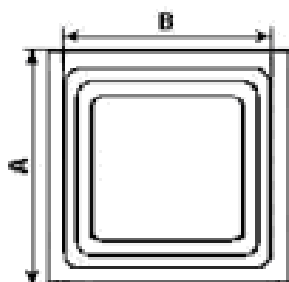


SCHOTTKY DIODES. KDS- 02015F.

PRELIMINARY.

Dec. 2012.

 VSP-MIKRON	2A/15V. Die Size-51mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_B	V	15	20
Average Rectified Forward Current	$I_{F(AV)}$	A	2,0	-
DC Forward Voltage @ 25°C, $I_F=2,0A$	V_F	V	0,38	0,36
Maximum Reverse Current @ 25°C, $V_R=15V$ @ 25°C, $V_R=20V$ 100°C, $V_R=15V$	I_R	MA	0,300 - 50,0	0,250 0,300 40,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	80	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150°C$.	I_{RRM}	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	125	



DIM	ITEM	µm
A _x A _y	Die Size	1300 1300
B _x B _y	Top Metal Size	1112 1112
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.